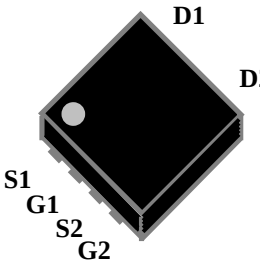
XP10A250YT

Halogen-Free Product

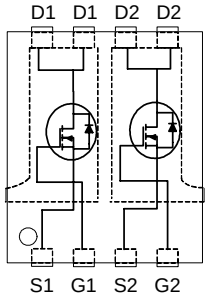
DUAL N-CHANNEL ENHANCEMENT MODE POWER MOSFET

- **Simple Drive Requirement**
- **Fast Switching Characteristic**
- **RoHS Compliant & Halogen-Free**



PMPAK® 3x3

BV_{DSS}	100V
$R_{DS(ON)}$	250mΩ
I_D [3]	2.1A



Description

XP10A250 series are innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The PMPAK ® 3x3 package is special for voltage conversion application using standard infrared reflow technique with the backside heat sink to achieve the good thermal performance.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Drain Current[3], V_{GS} @ 10V	2.1	A
I_D@T_A=70℃	Drain Current[3], V_{GS} @ 10V	1.7	A
I_{DM}	Pulsed Drain Current[1]	10	A
P_D@T_A=25℃	Total Power Dissipation	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Rating	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	10	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	50	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=2A	-	-	250	mΩ
		V_{GS}=4.5V, I_D=1A	-	-	500	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=2A	-	3	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V, V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=2A	-	5.5	8.8	nC
Q_{gs}	Gate-Source Charge	V_{DS}=50V	-	1.1	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	1.8	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=50V	-	6	-	ns
t_r	Rise Time	I_D=1A	-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	10	-	ns
t_f	Fall Time	V_{GS}=10V	-	6	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	200	320	pF
C_{oss}	Output Capacitance	V_{DS}=50V	-	25	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	20	-	pF
R_g	Gate Resistance	f=1.0MHz	-	2	4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=1.9A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_S=2A, V_{GS}=0V	-	30	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	24	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board, t ≤10sec ; 90 ℃/W on steady state.

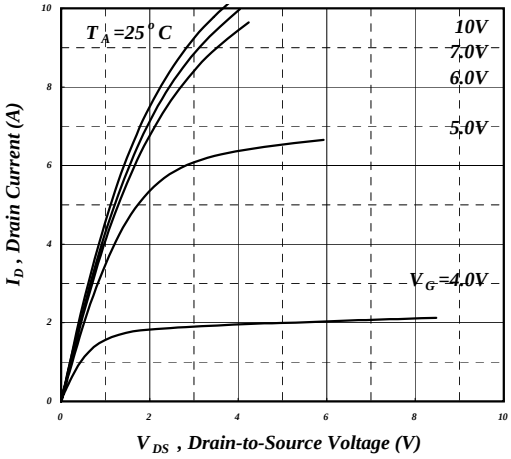


Fig 1. Typical Output Characteristics

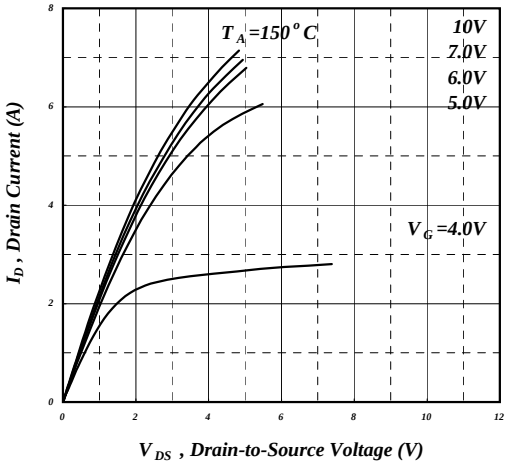


Fig 2. Typical Output Characteristics

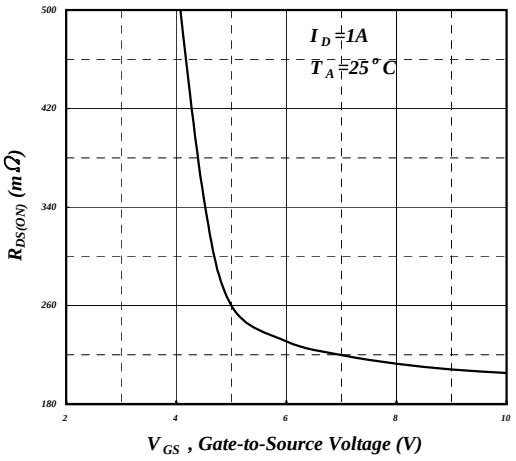


Fig 3. On-Resistance v.s. Gate Voltage

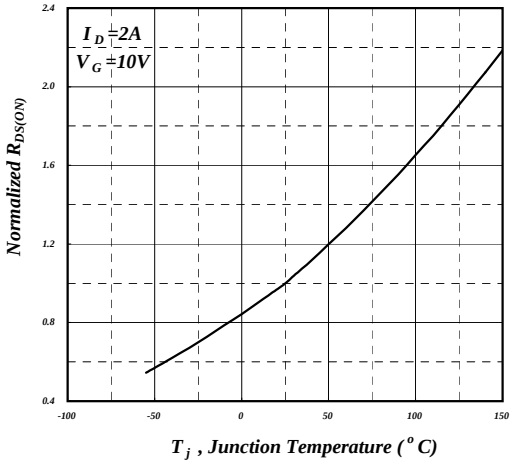


Fig 4. Normalized On-Resistance v.s. Junction Temperature

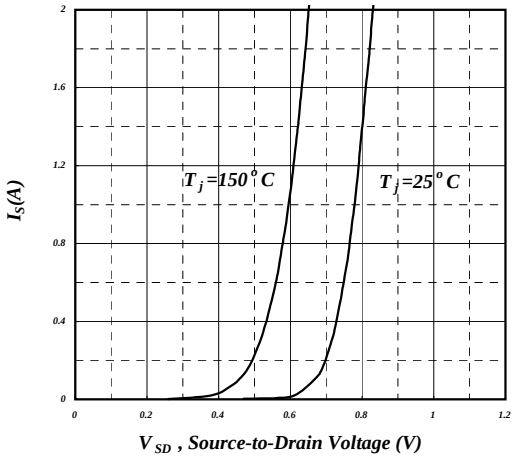


Fig 5. Forward Characteristic of Reverse Diode

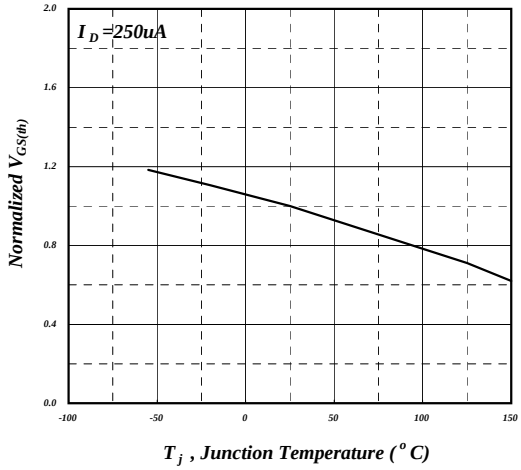


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

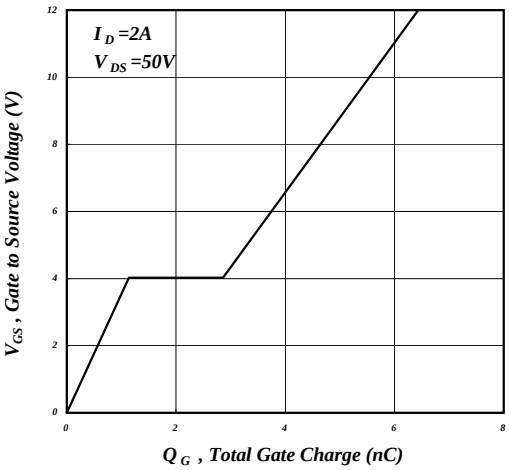


Fig 7. Gate Charge Characteristics

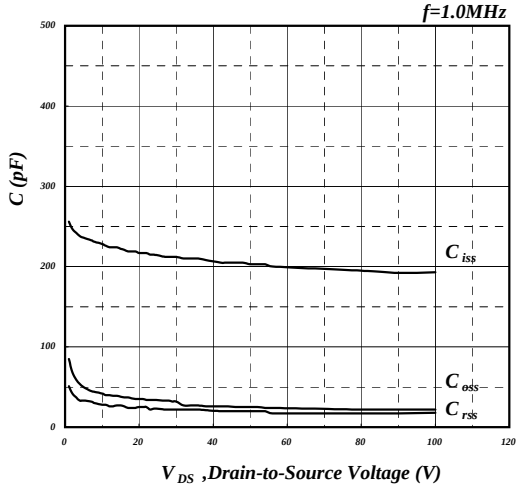


Fig 8. Typical Capacitance Characteristics

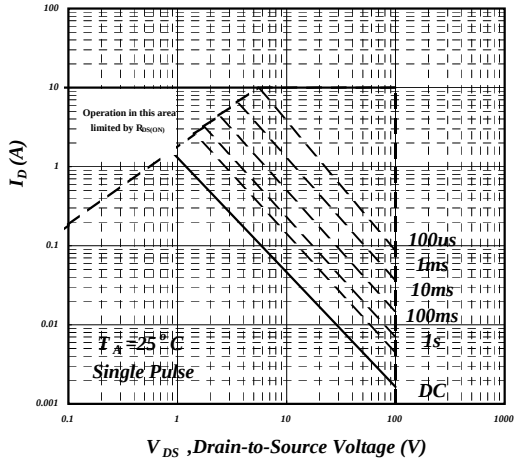


Fig 9. Maximum Safe Operating Area

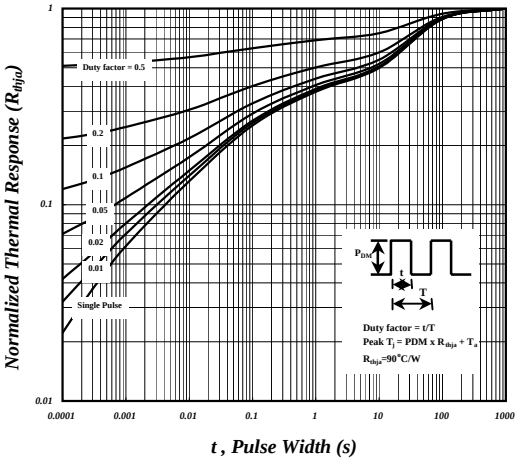


Fig 10. Effective Transient Thermal Impedance

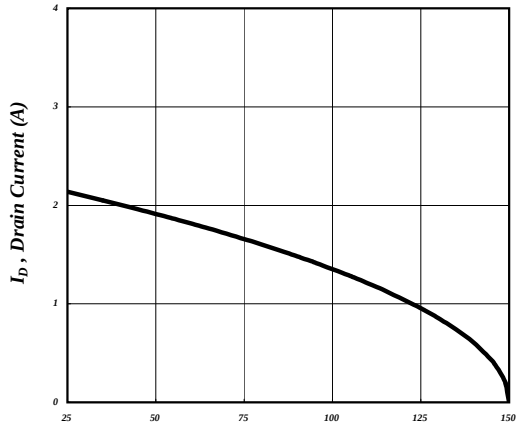


Fig 11. Drain Current v.s. Ambient Temperature

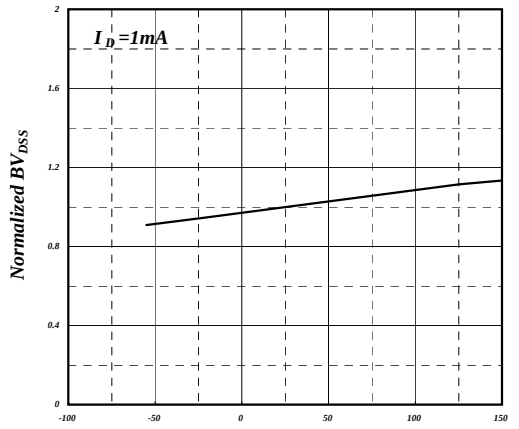


Fig 12. Normalized BV_{DSS} v.s. Junction Temperature